Attorney Docket No. 0025.0112 (TI-35881)

Application No.: 10/733,038

AMENDMENTS TO THE CLAIMS:

Applicants propose to amend claims 1, 12, 18 and 19; and cancel claims 7 and

18. No claims have been added. Claims 2-4 and 11 have been previously canceled.

Upon entry of this Response by the Examiner, this listing of claims will replace all prior

versions and listings of claims in the application.

1. (Currently Amended) An SRAM device, comprising:

an SRAM array coupled to row peripheral circuitry by a word line and coupled to

column peripheral circuitry by bit lines; and

an array low voltage control circuitry that provides an enhanced low operating

voltage V_{ESS} to said SRAM array during at least a portion of a READ operation or a

WRITE operation thereof, said enhanced low operating voltage V_{ESS} having a higher

value than a low operating voltage V_{SS}, and wherein said array low voltage control

circuitry provides said enhanced low operating voltage V_{ESS} at a lower value during said

READ operation than during said WRITE operation.

2. (Canceled).

(Canceled).

4. (Canceled).

-3-

Attorney Docket No. 0025.0112 (TI-35881) Application No.: 10/733.038

5. (Original) The SRAM device as recited in Claim 1 wherein array low voltage control circuitry provides said enhanced low operating voltage V_{ESS} based on a factor selected from the group consisting of:

a process corner.

a transistor parameter,

a mode of operation, and

a value of a high supply voltage,

 (Original) The SRAM device as recited in Claim 1 wherein said array low voltage control circuitry provides said enhanced low operating voltage V_{ESS} at a higher value when based on a strong n process corner.

(Canceled).

- (Currently Amended) The SRAM device as recited in Claim [[7]] 1 wherein said array low voltage control circuitry only provides said lower value for an addressed column of said SRAM array.
- (Original) The SRAM device as recited in Claim 1 wherein said array low voltage control circuitry employs an active component to provide said enhanced low operating voltage V_{ESS}.

Attorney Docket No. 0025.0112 (TI-35881) Application No.: 10/733.038

10. (Original) The SRAM device as recited in Claim 1 wherein said array low voltage control circuitry provides said enhanced low operating voltage V_{ESS} employing a component selected from the group consisting of:

a diode.

a transistor,

a fuse.

a ROM.

a voltage regulator, and

logic circuitry.

- (Canceled).
- 12. (Currently Amended) A method of operating an SRAM device, comprising: employing in an integrated circuit an SRAM array coupled to row peripheral circuitry by a word line and coupled to column peripheral circuitry by bit lines; and providing an enhanced low operating voltage V_{ESS} to said SRAM array during at least a portion of an active mode, said enhanced low operating voltage V_{ESS} having a higher value than a low operating voltage V_{SS}, and wherein said enhanced low operating voltage V_{ESS} is provided at a lower value during READ operation than during a WRITE operation.

Attorney Docket No. 0025.0112 (TI-35881) Application No.: 10/733,038

13. (Original) The method as recited in Claim 12 wherein said providing only occurs

during a WRITE operation.

14. (Original) The method as recited in Claim 12 wherein said providing occurs

during all of said active mode.

15. (Original) The method as recited in Claim 12 wherein said providing occurs

during all modes.

16. (Original) The method as recited in Claim 12 wherein said providing is based on

a factor selected from the group consisting of:

a process corner,

a transistor parameter,

a mode of operation, and

a value of a high supply voltage.

17. (Original) The method as recited in Claim 12 wherein said enhanced low

operating voltage V_{ESS} is provided at a higher value based on a strong n process

comer.

18. (Canceled).

-6-

Attorney Docket No. 0025.0112 (TI-35881) Application No.: 10/733.038

19. (Currently Amended) The method as recited in Claim [[18]] 12 wherein said lower value is only provided for an addressed column of said SRAM array.

 (Original) The method as recited in Claim 12 wherein said providing includes employing an active component to provide said enhanced low operating voltage V_{ESS}.

21. (Original) The method as recited in Claim 12 wherein said providing includes employing a component selected from the group consisting of:

a diode.

a transistor.

a fuse.

a ROM.

a voltage regulator, and

logic circuitry.